查询SN75LBC968供应商

Nine Single-Ended SCSI Transceiver

专业PCB打样工厂,24小时加急出SN75LBC968 9-CHANNEL BUS TRANSCEIVER WITH ACTIVE TERMINATION SLLS179C - APRIL 1994 - REVISED JANUARY 1999

DL PACKAGE

Channels With Active Termination	(TOP VIEW)			
Programmable Drivers Provide Active Negation (Totem Pole) or Wired-OR (Open	GND [TE [1 2		8B GND
Drain) Outputs 24-mA Current-Mode Active Termination	GND			CE NC
With Common Nine-Channel Bus Enable	1DE/RE		- E	NC
Low Output Capacitance Presented to SCSI Bus, 13.5 pF Typ	2A [2DE/RE [6 7] NC] 7B
3.3 V Compatible Logic Inputs Provide Bridge from 3 V Controllers to 5 V SCSI	3A [3DE/RE [8 9	- 6] NC] 6B
Bus	4A	10] NC
Designed to Operate at 10-Million Data Transfers Per Second (Fast-SCSI)	4DE/RE	11 12	45	5B V _{CC}
Controlled Driver Rise and Fall Times 5 ns Min	GND GND	13 14	43	GND GND
High-Receiver Input-Voltage Hysteresis 500 mV Typ	GND GND	15 16 17	41] GND] GND] GND
Receiver Input-Noise Pulse Filter 5 ns Typ	GND [V _{CC} [5A [18 19	39] V _{CC}] NC
Each Driver and Receiver Meets ANSI X3.131-1994 (SCSI-2) and the Proposed	5DE/RE [6A [20 21	37] 4B] NC
SCSI-3 Standards	6DE/RE	22	E] 3B
Power-Up/Power-Down Glitch Protection	7A [23 24	34 33	NC
High Impedance Driver With V _{CC} at 0 V	7DE/RE	24	- H	2B
ription	8DE/RE	26 27	31 30	1B
The SN75LBC968 is a nine-channel transceiver	9A L 9DE/RE [28	29	

description

The SN75LBC968 is a nine-channel transceiver with active termination that drives and receives the signals from the single-ended, parallel data buses such as the Small Computer-Systems

NC - No internal connection

Interface (SCSI) bus. The features of the line drivers, receivers, and active-termination circuits provide the optimum signal-to-noise ratios for reliable data transmission. Integration of the termination and transceivers in the LinBiCMOS™ process provides the necessary analog-circuit performance, has low quiescent power, and reduces the capacitance presented to the bus over separate termination and I/O circuits.

The transceivers of the SN75LBC968 can be enabled to function as totem-pole or open-drain outputs. The open-drain mode drives the wired-OR lines of SCSI (BSY, SEL, and RST) by inputting the data to the direction control input DE/RE instead of the A input. When driving the data through the A input, the outputs become totem poles and provide active signal negation for a higher voltage level on low-to-high signal transitions on heavily loaded buses. In either mode, the turn-on and turn-off output transition times are limited to minimize crosstalk through capacitive coupling to adjacent lines and RF emissions from the cable. The receivers are also designed for optimum analog performance by precisely controlling the input-voltage thresholds, providing wide input-voltage hysteresis and including an input-noise filter. These features significantly increase the likelihood of detecting only the desired data signal and rejecting noise.



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RODUCTION DATA information is current as of publication date reducts conform to specifications per the terms of Texas Instruments tandard warranty. Production processing does not necessarily include esting of all parameters.



description (continued)

The communication between the SN75LBC968 and the controller can be accomplished at 3.3-V logic levels provided that the V_{CC1} input connects to the same supply rail as the controller. This provides a bridge from the lower-voltage circuit and the 5-V SCSI bus. The SN75LBC968 also removes the need for special I/O buffers (and associated power dissipation) on the controller itself. The SN75LBC968 must be used with a SCSI controller with support for Differential SCSI.

The integrated, current-mode, active termination supplies a constant 24 mA of current (TERMPWR) to the bus when the bus voltage falls below 2.5 V. This makes the next low-to-high (negation) signal transition independent of the low-level (asserted) bus voltage, unlike voltage-mode terminators. The termination current is provided through the TE input and from TERMPWR and can be disabled by letting the TE input float or by connecting it to ground. The termination circuitry is independent from the line drivers and receivers and V_{CC} or V_{CC1}. Operational termination is present as long as TERMPWR is applied.

The switching speeds of the SN75LBC968 are sufficient to transfer data over the data bus at ten million transfers per second (Fast-SCSI). The specification, $t_{sk(lim)}$, is for system skew budgeting and maintenance of bus set-up and hold times. The device is available in the space-efficient shrink-small-outline package (SSOP) with 25-mil lead pitch. The SN75LBC968 meets or exceeds the requirements of ANSI X3.131–1994 (SCSI-2) and the proposed SPI (SCSI-3) standards, and is characterized for operation from 0°C to 70°C.

Active Terminator 2 TE 4 <u>31</u> 1B **1**A 5 1DE/RE 54 CE 6 <u>33</u> 2B 2A 7 Channel 2 2DE/RE 8 35 3B 3A 9 Channel 3 3DE/RE 10 37 4B 4A **Channel 4** 11 4DE/RE 19 <u>46</u> 5B 5A Channel 5 20 5DE/RE 21 48 6B 6A 22 Channel 6 6DE/RE 50 7B 23 7A Channel 7 24 7DE/RE 25 56 — 8B **8**A 26 Channel 8 8DE/RE 27 29 9B 9A Channel 9 28 9DE/RE

logic diagram (positive logic)

Function Tables TRANSCEIVER FUNCTIONS

	IN	OUT	PUTS		
CE	DE/RE	Α	В	Α	В
L	Х	Х	Х	Z	Z
н	L	Х	L	н	Z
н	L	Х	Н	L	Z
н	Н	L	Х	Z	Н
н	Н	Н	Х	Z	L
н	L	Х	Open	Н	Z
Н	Н	Open	Х	Z	L

H = high level L = low level

X = irrelevant Z = high impedance

TERMINATION FUNCTION

INPUT TE	OUTPUT B
GND	Z
VTE	24-mA source
Open	Z



 DRIVER
 ACTIVE TERMINATOR

 VCC
 TE

 2.85 V
 TE

 777
 TE

 777
 TT

 777
 TT

schematics

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC} , V _{CC1} , V _{TE} (see Note 1)	0.5 V to 7 V
Input voltage range, V _I (A-side)	V _{CC1} + 0.3 V
Bus voltage range (B-side)	–0.5 V to 7 V
Data I/O and control (A-side) voltage range	0.5 V to 7 V
Continuous power dissipation (see Note 2)	Internally Limited
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range, T _{stg}	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to GND.

2. The maximum operating-junction temperature is internally limited. Use the dissipation rating table to operate below this temperature.



SN75LBC968 9-CHANNEL BUS TRANSCEIVER WITH ACTIVE TERMINATION

SLLS179C - APRIL	1994 – REVISED JANUARY 1999	1

DISSIPATION RATING TABLE					
PACKAGE	$T_A \le 25^{\circ}C$ POWER RATING	DERATING FACTOR [†] ABOVE T _A = 25°C	T _A = 70°C POWER RATING		
DL	2500 mW	20 mW/°C	1600 mW		

[†] Derating factors are the inverse of the junction-to-ambient thermal resistance when board-mounted with no air flow.

recommended operating conditions

		MIN	NOM	MAX	UNIT	
Supply voltage, V _{CC}		4.75	5	5.25	V	
Supply voltage, V _{CC1} (see Note 3)		3		5.25	V	
Termination voltage, V _{TE}		4.25		5.25	V	
High-level input voltage, VIH	DE/RE, CE, A, B	2			V	
Low-level input voltage, VIL	DE/RE, CE, A, B			0.8	V	
High-level output current, I _{OH}	A			-8	mA	
	В			48		
Low-level output current, IOL	A			8	mA	
Operating free-air temperature, T _A		0		70	°C	

NOTE 3: All electrical characteristics are measured with V_{CC1} = V_{CC} unless otherwise noted.

driver electrical characteristics over recommended operating conditions (unless otherwise noted) (see Figure 1)

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
VOH	High-level output voltage	$I_{OH} = -20 \text{ mA}$	2		V
VOL	Low-level output voltage	I _{OL} = 48 mA		0.5	V
Чн	High-level input current	$V_{IH} = 2 V$, $V_{CC} = V_{CC1} = 5.25 V$		-100	μΑ
١ _{١L}	Low-level input current, A	$V_{IL} = 0.5 V$, $V_{CC} = V_{CC1} = 5.25 V$		-100	μΑ
	High impedance state output current	$V_{O} = 5.25 \text{ V}, \qquad V_{CC} = V_{CC1} = 5.25 \text{ V}$		-100	μA
102	IOZ High-impedance-state output current	$V_{O} = 0 V$, $V_{CC} = V_{CC1} = 5.25 V$		-100	μΑ

termination electrical characteristics over recommended operating conditions (unless otherwise noted) (see Figure 2)

	PARAMETER	TES	T CONDITIONS	MIN	TYP	MAX	UNIT
VO(OC)	Open-circuit output voltage	IO = 0 mA,	VCC = V CC1 = 0 V	2.5	2.85	3.24	V
	Output current	$V_{O} = 0 V,$	VCC = V CC1 = 0 V			-24	mA
		V _O = 0.5 V,	$V_{CC} = V_{CC1} = 0 V$	-20		-24	mA
10		V _O = 3 V,	$V_{CC} = V_{CC1} = 0 V$			100	μΑ
		V _O = 4 V,	$V_{CC} = V_{CC1} = 0 V$	2		12	mA



receiver electrical characteristics over recommended operating conditions (unless otherwise noted) (see Figure 3)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOH	High-level output voltage	I _{OH} = -8 mA	2	2.5		V
VOL	Low-level output voltage	I _{OL} = 8 mA			0.8	V
VIT+	Positive-going input threshold voltage		1.2	1.6	2	V
V _{IT} -	Negative-going input threshold voltage	VCC = VCC1	0.8	1.1	1.4	V
V _{hys}	Input hysteresis voltage (VIT+ - VIT-)		0.2	0.5		V
Чн	High-level input current	VIH = 2 V			100	μA
۱ _{IL}	Low-level input current	V _{IL} = 0.5 V			100	μΑ
	High impodance state output current	$V_{O} = 0 V$			-100	μA
loz	High-impedance-state output current	V _O = 5.25 V			-100	μΑ

device electrical characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN TYP [†]	MAX	UNIT
	All drivers, receivers, and terminator disabled	All inputs at 0 V	1.3	3		
	Supply current to V _{CC}	drivers disabled, No load T All drivers enabled, termination and receivers disabled, No load D V Termination and receivers enabled	CE at V _{CC} , DE/ RE at 0 V, TE at 0 V	14	21	
ICC	and V _{CC1}		DE/RE and CE at V _{CC} , A and TE at 0 V	33	45	mA
			DE/\overline{RE} and CE at V _{CC} , V _{TE} = 0 V, A at V _{CC1}	15	21	
ICC	Supply current to TE		TE at V_{TE} , DE/ \overline{RE} at 0 V	33	45	
Co	Bus port capacitance (se	ee Note 4)		13.5	16.5	рF
Iн	High-level input current	DE/RE, CE	$V_{IH} = V_{CC} \text{ or } 2 \text{ V}$		100	μΑ
١ _{IL}	Low-level input current	DE/RE, CE	V _{IL} = 0.5 V		100	μΑ

[†] All typical values are at $V_{CC} = V_{CC1} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$. NOTE 4: Tested in accordance with Annex G X3T9.2/855D, revision 14



driver switching characteristics over recommended energing

driver switching characteristics over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP [†]	MAX	UNIT
^t PHL	Propagation delay time, high- to low-level output (see Figure 4)	C1 = 15 pF	10		35	ns
^t PLH	Propagation delay time, low- to high-level output (see Figure 4)		15		45	ns
*	Skew limit [‡] , the maximum delay time – minimum delay	$V_{CC} = V_{CC1} = 5 \text{ V}, T_A = 25^{\circ}\text{C},$ $C_L = 15 \text{ pF}$			14	ns
^t sk(lim)	time $V_{CC} = V_{CC1} = 5 \text{ V}, \text{ T}_A = 70^{\circ}\text{C},$ $C_L = 15 \text{ pF}$				14	ns
^t sk(p)	Pulse skew, tpHL - tpLH	$V_{CC} = V_{CC1} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$		8		ns
t _t	Output transition time, 10% to 90% or 90% to 10% of the steady-state output	15 pF < C _L < 100 pF	5		20	ns
to	Propagation delay time, low-level to high-impedance	From CE, $C_L = 15 \text{ pF}$	5		150	50
^t PLZ	output (see Figure 5)	From DE/RE, $C_L = 15 \text{ pF}$			45	ns
t	Propagation delay time, high-impedance to low-level	From CE, $C_L = 15 \text{ pF}$	5		150	
^t PZL	output (see Figure 5)	From DE/ \overline{RE} , $C_L = 15 \text{ pF}$			45	ns

[†] All typical values are at $V_{CC} = V_{CC1} = 5 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C}.$

[‡] The value for this parameter was derived from the difference between the slowest and the fastest driver delay times measured on devices from four sample wafer lots.

receiver switching characteristics over recommended of operating conditions (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	MIN	TYP†	MAX	UNIT
^t PHL	Propagation delay time, high- to low-level output	See Figure 6		5		20	ns
^t PLH	Propagation delay time, low- to high-level output			5		25	ns
^t sk(lim)	Skew limit [‡] , the maximum delay time – minimum delay time	$V_{CC} = V_{CC1} = 5 V,$ See Figure 6	$T_A = 25^{\circ}C$,			8.5	ns
		$V_{CC} = V_{CC1} = 5 V,$ See Figure 6	$T_A = 70^{\circ}C$,			8.5	ns
t _{sk(p)}	Pulse skew, tpHL - tpLH	$V_{CC} = V_{CC1} = 5 V,$ See Figure 6	$T_A = 25^{\circ}C$,		6		ns
^t PLZ	Propagation delay time, low-level to high-impedance output	From CE,	See Figure 7	5		150	ns
		From DE/RE,	See Figure 7			45	
^t PZL	Propagation delay time, high-impedance to low-level output	From CE,	See Figure 7	5		150	ns
		From DE/RE,	See Figure 7			80	
^t PHZ	Propagation delay time, high-level to high-impedance output	From CE,	See Figure 8	5		150	ns
		From DE/RE,	See Figure 8			45	
^t PZH	Propagation delay time, high-impedance to high-level output	From CE,	See Figure 8	5		150	ns
		From DE/RE,	See Figure 8			80	

[†] All typical values are at $V_{CC} = V_{CC1} = 5 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C}.$

[‡] The value for this parameter was derived from the difference between the slowest and the fastest driver delay times measured on devices from four sample wafer lots.

thermal characteristics

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-free-air thermal resistance	Board-mounted, no air flow		50		°C/W
$R_{\theta JC}$	Junction-to-case thermal resistance			12		°C/W
TJS	Junction-shutdown temperature			180		°C



PARAMETER MEASUREMENT INFORMATION

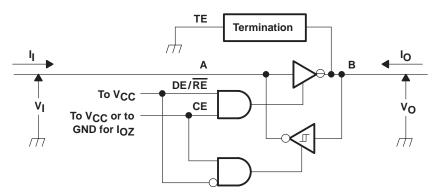


Figure 1. Driver Test Circuit Currents and Voltages.

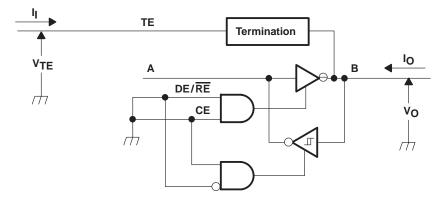


Figure 2. Active Termination Voltages, Currents, and Test Circuit.

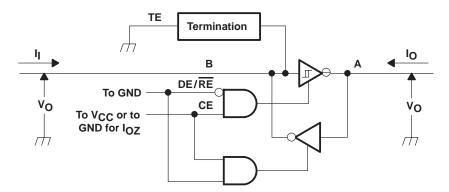
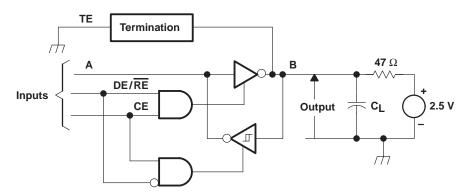


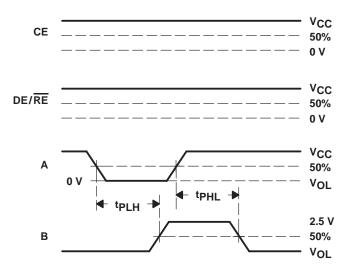
Figure 3. Receiver Voltages, Currents, and Test Circuit

- NOTES: A. All input pulses are supplied by a generator having the following characteristics: $t_f \le 6$ ns, $t_f \le 6$ ns, PRR ≤ 1 MHz, duty cycle = 50%, $Z_O = 50 \Omega$.
 - B. All resistances are in ohms and $\pm 5\%$, unless otherwise indicated.
 - C. All capacitances are in picofarads and $\pm 10\%$, unless otherwise indicated.
 - D. All indicated voltages are ± 10 mV.



PARAMETER MEASUREMENT INFORMATION

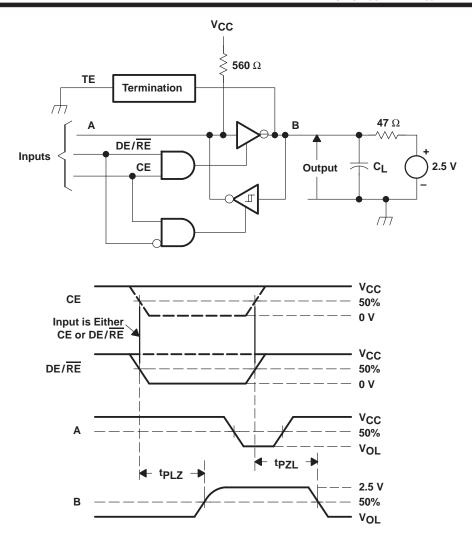




- NOTES: A. All input pulses are supplied by a generator having the following characteristics: $t_{f} \leq 6$ ns, $t_{f} \leq 6$ ns, PRR ≤ 1 MHz, duty cycle = 50%, Z_{O} = 50 Ω .
 - B. All resistances are in ohms and \pm 5%, unless otherwise indicated.
 - C. All capacitances are in picofarads and $\pm 10\%$, unless otherwise indicated.
 - D. All indicated voltages are ± 10 mV.

Figure 4. Driver Delay Time Test Circuit and Waveforms

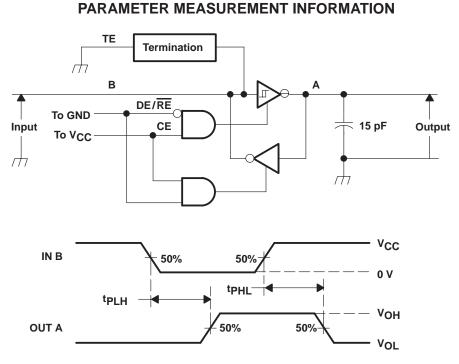




- NOTES: A. All input pulses are supplied by a generator having the following characteristics: $t_{\Gamma} \le 6$ ns, $t_{f} \le 6$ ns, PRR ≤ 1 MHz, duty cycle = 50%, Z_{O} = 50 Ω .
 - B. All resistances are in ohms and $\pm 5\%$, unless otherwise indicated.
 - C. All capacitances are in picofarads and $\pm 10\%$, unless otherwise indicated.
 - D. All indicated voltages are ± 10 mV.

Figure 5. Driver Delay Time Test Circuit and Waveforms



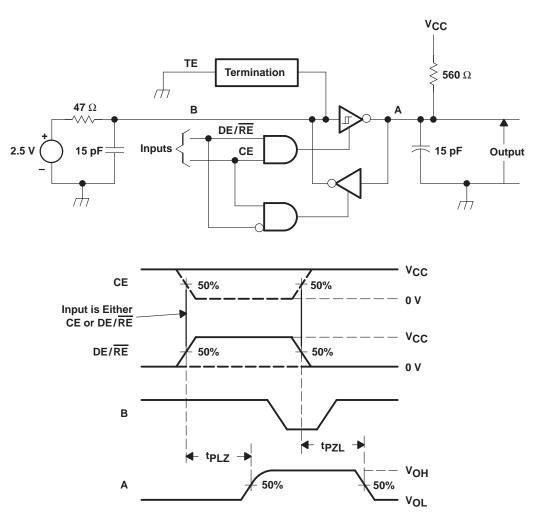


NOTES: A. All input pulses are supplied by a generator having the following characteristics: $t_f \le 6$ ns, $t_f \le 6$ ns, PRR ≤ 1 MHz, duty cycle = 50%, $Z_O = 50 \Omega$.

- B. All resistances are in ohms and $\pm 5\%$, unless otherwise indicated.
- C. All capacitances are in picofarads and $\pm 10\%$, unless otherwise indicated.
- D. All indicated voltages are ± 10 mV.

Figure 6. Receiver Propagation Delay Time Test Circuit and Waveforms



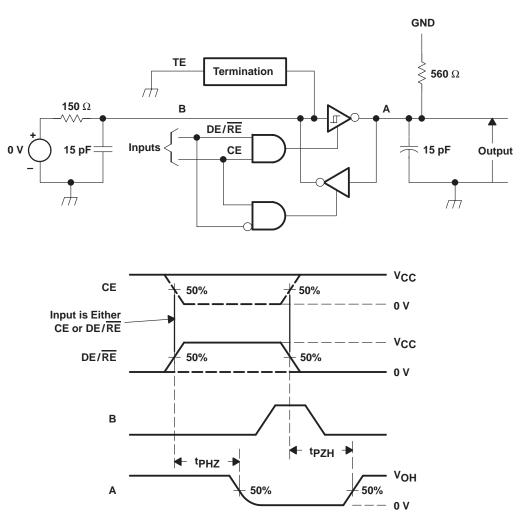


PARAMETER MEASUREMENT INFORMATION

- NOTES: A. All input pulses are supplied by a generator having the following characteristics: $t_{f} \leq 6$ ns, $PRR \leq 1$ MHz, duty cycle = 50%, $Z_O = 50 \Omega$.
 - B. All resistances are in ohms and $\pm 5\%$, unless otherwise indicated.
 - C. All capacitances are in picofarads and $\pm 10\%$, unless otherwise indicated.
 - D. All indicated voltages are ± 10 mV.

Figure 7. Receiver Enable and Disable Times to and From Low-Level Output Test Circuit and Waveforms





PARAMETER MEASUREMENT INFORMATION

NOTES: A. All input pulses are supplied by a generator having the following characteristics: $t_{f} \leq 6$ ns, $t_{f} \leq 6$ ns, $PRR \leq 1$ MHz, duty cycle = 50%, $Z_O = 50 \Omega$.

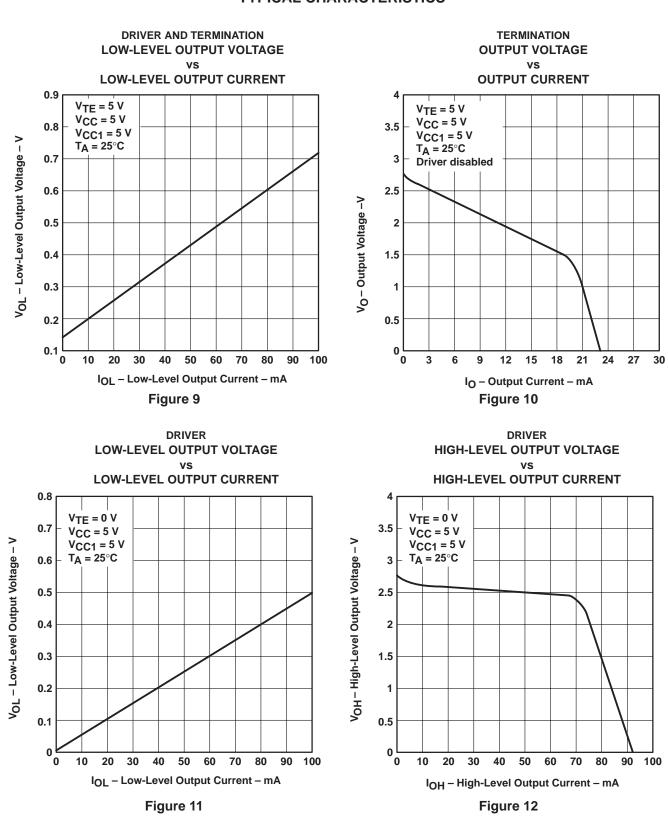
B. All resistances are in ohms and $\pm 5\%$, unless otherwise indicated.

C. All capacitances are in picofarads and $\pm 10\%$, unless otherwise indicated.

D. All indicated voltages are ± 10 mV.

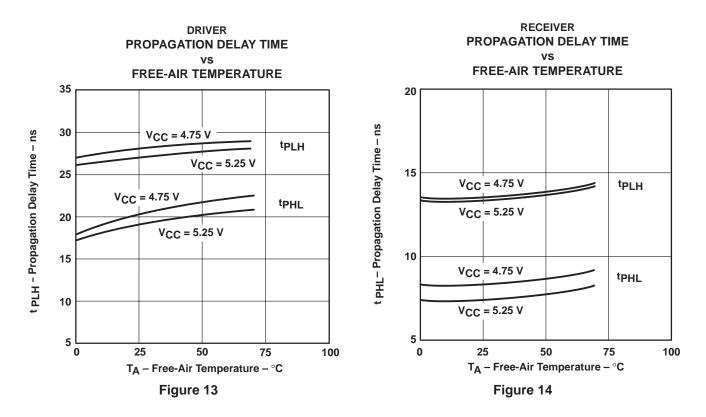
Figure 8. Receiver Enable and Disable Times to and From High-Level Output Test Circuit and Waveforms





TYPICAL CHARACTERISTICS



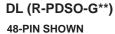


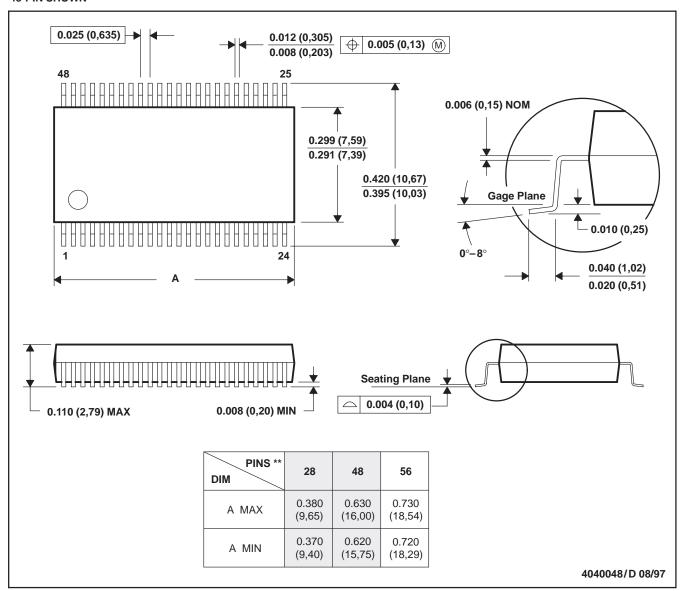
TYPICAL CHARACTERISTICS



MECHANICAL DATA

PLASTIC SMALL-OUTLINE PACKAGE





NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MO-118



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